

Optical modeling of polysilicon: TOPCon PV

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Introduction

Tunnel Oxide Passivated Contact (TOPCon)

- Utilizes n-type silicon substrate, a thin tunnel oxide, and a polysilicon layer to provide surface passivation.
- Passivation prevents defects and recombination.

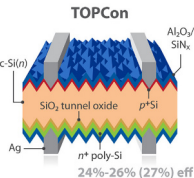


Fig 1: TOPCon solar cell

TOPCon Advantages:

- High conversion efficiency (25%)
- Better energy yields in variable weather conditions (e.g., high temperature, shade).

Research Goal:

- Determine how film thickness changes with different deposition methods.
- Analyze relationship between film thickness and optical constants.

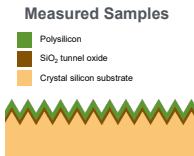


Fig 2: Polysilicon on silicon tunnel oxide on a crystal silicon substrate

Spectroscopic Ellipsometry

- Non-destructive method to determine thin-film thickness and optical properties.
- Measures a time-modulated intensity signal and determines changes in polarization.

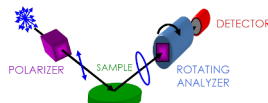


Fig 3: Interactions with the sample polarize the light. Reflected polarized light is measured by the rotating analyzer and detector.

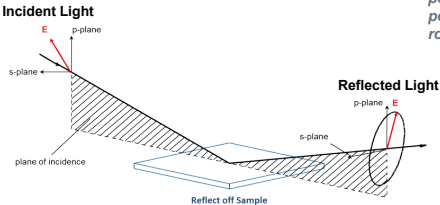


Fig 4: Polarized light traces a repeating path in the perpendicular plane (s-plane).

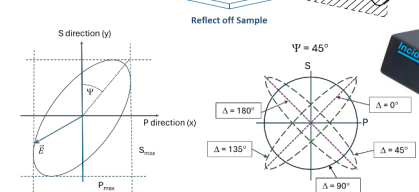


Fig 5 and 6: The relative phase difference between two orthogonal electric field components, and the amplitudes of the orthogonal electric field components, determines the shape of the ellipse.

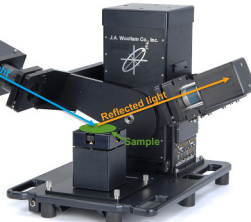


Fig 7: J.A. Woollam M-2000 Spectroscopic Ellipsometer

Methods

Bruggeman Effective Medium Approximation (EMA):

- Models the optical constants of a two-phase composite by blending the optical constants of two defined materials.
- Corresponds to a medium with varying sized spherical inclusions.

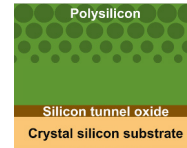


Fig 8: Sample Model

General Oscillator (Gen-OSC):

- Used to parameterize materials to model complex, amorphous, and/or unknown materials.
- Determines the optical constants of a material by manipulating absorption and dispersion parameters of a reference material.

- Fixed thickness and optical constants

Polysilicon:

- EMA blends optical constants of hydrogenated amorphous silicon and crystal silicon
- Parameterized as general oscillator to fine tune optical constants
- Fitted thickness

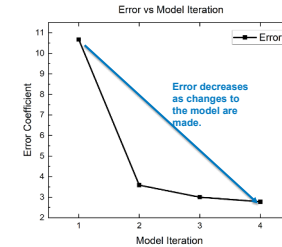


Fig 9: Lower error coefficient means better model fit

- Changes with each iteration:
- Best EMA no optical fitting, fit film thickness
 - EMA fit optical constants
 - Parameterized as general oscillator
 - Added and fit for surface roughness

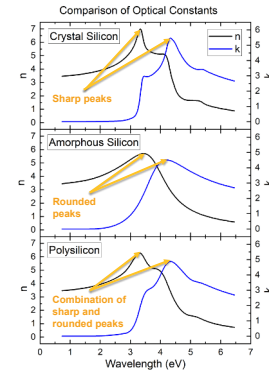


Fig 10: Wavelength's optical constants are based on the optical constants of crystal silicon and amorphous silicon

Results

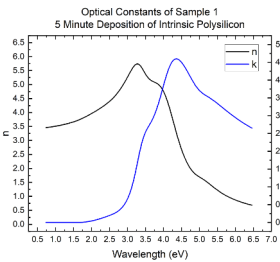


Fig 11: Sample 1 – 5 minute deposition of intrinsic polysilicon
Polysilicon thickness: 11.55 nm
Surface Roughness: 2.15 nm
Error Coefficient: 2.253

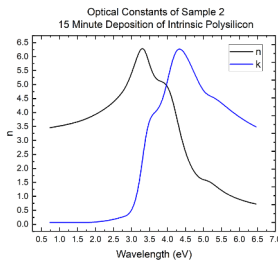


Fig 12: Sample 2 – 15 minute deposition of intrinsic polysilicon
Polysilicon thickness: 26.45 nm
Surface Roughness: 1.25 nm
Error Coefficient: 3.258

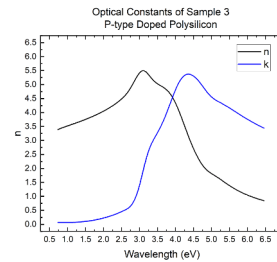


Fig 13: Sample 3 – P-type doped polysilicon
Polysilicon thickness: 29.26 nm
Surface Roughness: 2.34 nm
Error Coefficient: 2.465
TEM polysilicon thickness: ~29nm

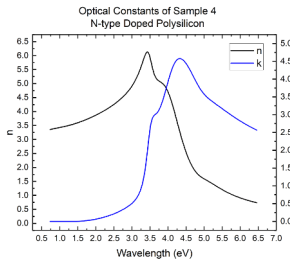


Fig 14: Sample 4 – N-type doped polysilicon
Polysilicon thickness: 28.10 nm
Surface Roughness: 1.49 nm
Error Coefficient: 3.002

Conclusions

- The deposition rate of intrinsic polysilicon is higher during initial deposition then begins to slow down as deposition time increases.
- Longer depositions of polysilicon are more crystalline in structure than shorter depositions. N-type doping of polysilicon is more crystalline in structure than P-type doping, despite similar film thicknesses.

Future Work

Deposition of alumina on top of polysilicon then annealing. Spectroscopic ellipsometry results of such work will provide further understanding of deposition rates and will help fine tune current deposition methods and equipment.